Message ID: **114** Entry time: **5/6/2021 10:54:55 AM**

Experiment Date:	2020 05 18
Duration (Days):	2
User:	M. Barac, Z. Siketic
Accelerator:	Tandetron
Beam Line:	Old uProbe
Project:	RADIATE JRA (H2020 projekt)
Experiment Title:	LE MeV SIMS Ar sputter cleaning + yield meas. of various inorganic samples
Beam:	5 MeV Si4+
Method:	MeV SIMS

SETUP:

Me = 49.3; Ox = 32.4

x = 1.5; y = 7

colim. slits: +20 rounds

V_chopper = +-500 V

chopper high = 100 us

chopper low = 100 us

1 channel = 3.33 ns

V_ext = +5 kV

V_det = -5 kV

file	sample	I_before / kHz	I_after / kHz	notes
2005094	CsI, positive mode	84	87	
2005095	CsI, negative mode	87	84.7	
2005096	Sn	84.7	-	
Ar sputtering Sn, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005097	clean Sn	-	89	
2005099	Co	89	-	
Ar sputtering Co, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005100	clean Co	-	86	
2005101	HfO2	86	-	
Ar sputtering HfO2, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005102	clean HfO2	-	67	
2005103	MgO	67	74	
2005104	Zr	87	-	
Ar sputtering Zr, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005105	clean Zr	-	90	
2005106	ZrO2	90	-	
Ar sputtering ZrO2, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005107	clean ZrO2	-	89	
2005108	Ti bulk	89	-	

Ar sputtering Ti, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005109	clean Ti	-	86	
2005110	TiO2	86	-	
Ar sputtering TiO2, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005111	clean TiO2	-	90.5	
2005112	ITO	90.5	-	
Ar sputtering ITO, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005113	clean ITO	-	89.8	
2005114	In	99.7	-	
Ar sputtering In, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005115	clean In	-	98	
2005116	Li	98	87	
2005117	V	87	-	
Ar sputtering V, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005118	clean V	-	90	
2005119	Cr	90	-	
Ar sputtering Cr, E= 3 keV, I_e = 10 mA, t = 15 min, dp = 6.3 x10-6 mbar				
2005120	clean Cr	-	73	